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PATENT, TRADEMARK & COPYRIGHT ATTORNEYS

P.O. Box 2938

Minneapolis, MN 55402

Telephone (612) 373-6900 Facsimile (612) 339-3061

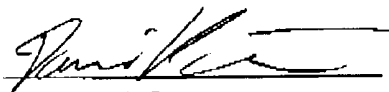
May 7, 2001

Time: 11:05 am
(Minneapolis, Minn.)TO: Commissioner for Patents
Attn: Karabi Guharay
Patent Examining Corps
Facsimile Center
Washington, D.C. 20231FROM: David C. PetersonOUR REF: 303.537US1TELEPHONE: (612) 373-6944FAX NUMBER (703) 746-4822*** Please deliver to Examiner Karabi Guharay in Art Unit 2879. ***Document(s) Transmitted: Signed copy of previously filed Amendment and Response (7 pgs.)Total pages of this transmission, including cover letter: 8 pgs


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In re. Patent Application of: Ji Ung LeeExaminer: Karabi GuharaySerial No.: 09/145,595Group Art Unit: 2879Filed: September 2, 1998Docket No.: 303.537US1Title: FIELD EMISSION DEVICES HAVING STRUCTURE FOR REDUCED EMITTER
TIP TO GATE SPACING

Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

By: 
Name: David C. Peterson
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Tina M. Pugh5/7/01
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EXPEDITED PROCEDURE - EXAMINING GROUP 2879**S/N 09/145,595****PATENT****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Ji Ung Lee	Examiner:	Karabi Guharay
Serial No.:	09/145,595	Group Art Unit:	2879
Filed:	September 2, 1998	Docket:	303.537US1
Title:	FIELD EMISSION DEVICES HAVING STRUCTURE FOR REDUCED EMITTER TIP TO GATE SPACING		

AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116

Box AF
Commissioner for Patents
Washington, D.C. 20231

In response to the Final Office Action mailed February 22, 2001, please amend the application as follows:

IN THE CLAIMS

Please add the following new claims:

47. (New) A field emitter array, comprising:
a number of cathodes in rows along a substrate;
a gate insulator located along the substrate and surrounding the cathodes, the gate insulator having a gate line region thickness;
a number of gate lines coupled to the gate insulator, wherein a gate to cathode distance between a portion of the gate line and the cathode is substantially thinner than the gate line region thickness ; and
a number of anodes located in columns orthogonal to and opposing the rows of cathodes.
48. (New) The field emitter array of claim 47, wherein the number of cathodes include polysilicon cones.
49. (New) The field emitter array of claim 47, wherein the number of gate lines include refractory metals.